

What is claimed is:

1. A semiconductor device comprising:
a substrate;
5 a seal layer which seals a semiconductor element formed on the substrate,
wherein a side surface of the seal layer is positioned inside of a side surface
of the substrate.
2. The semiconductor device according to claim 1, wherein the side surface
10 of the seal layer has a cut cross-section formed by grinding, and the side surface of
the substrate has a cut cross-section formed by applying laser light to the substrate.
3. The semiconductor device according to claim 1, wherein the side surface
of the seal layer is positioned inside of the side surface of the substrate within a
15 range of 5 μ m to 100 μ m.
4. The semiconductor device according to claim 1, wherein the substrate is a
silicon substrate or a sapphire substrate whose surface is formed with a silicon thin
film.
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5. A semiconductor device comprising:
a substrate;
a sealing resin sealing a semiconductor element formed on the substrate,
wherein a side surface of the sealing resin is positioned inside of a side
25 surface of the substrate.
6. The semiconductor device according to claim 5, wherein the side surface

of the sealing resin has a cut cross-section formed by grinding, and the side surface of the substrate has a cut cross-section formed by applying laser light to the substrate.

7. The semiconductor device according to claim 5, wherein the side surface
5 of the sealing resin is positioned inside of the side surface of the substrate within a range of 5 μ m to 100 μ m.

8. The semiconductor device according to claim 5, wherein the substrate is a
silicon substrate or a sapphire substrate whose surface is formed with a silicon thin
10 film.

9. A semiconductor device comprising:
a substrate which has a main surface formed with a circuit element;
a wiring which is formed over the main surface and which is electrically
15 connected to the circuit element;
a sealing resin which covers the main surface of the substrate and the wiring; and
an external terminal which is electrically connected to the wiring and which
is exposed from a surface of the sealing resin,
20 wherein an edge of the sealing resin is formed inside an edge of the substrate.

10. The semiconductor device according to claim 9, wherein a side surface of the sealing resin has a cut cross-section formed by grinding, and a side surface of the
25 substrate has a cut cross-section formed by applying laser light to the substrate.

11. The semiconductor device according to claim 9, wherein the side surface

of the sealing resin is positioned inside of a side surface of the substrate within a range of 5 μ m to 100 μ m.

12. The semiconductor device according to claim 9, wherein the substrate is
5 a silicon substrate or a sapphire substrate whose surface is formed with a silicon thin film.

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